Physics 601

		4		
M	Id	TO	rm	١

October 23, 2015

Name	Solutions	
_		

The five problems are worth 20 points each.

particular and the second seco	
Problem	Score
1	
2	
3	
4	
5	
Total	



- 1. Temperature-Dependence of the Bragg angle for AI. At 300 K, AI has an fcc structure with a lattice constant of 0.405 nm. The coefficient of heat expansion for AI is $\alpha = 25 \times 10^{-6} \, \text{K}^{-1}$. Aluminum is studied with Cu K radiation which has a wavelength of $\lambda = 0.154$ nm. Let's now investigate the change $\Delta \Theta$ in Θ due to the change in temperature from 300 to 600 K.
- (a) Derive the expression for $\Delta\theta$ in terms of θ

$$\Delta a = \Delta \Delta T = (25 \times 10^{-6} \text{ K}^{-1}) (300 \text{ K})$$

$$= 7.5 \times 10^{-3}$$

$$sim^2 O = (h^2 + k^2 + l^2) \lambda^2$$

$$2 \sin \theta \cos \theta d\theta = -\frac{\lambda^2}{2a^3} \left(\frac{h^2 + k^2 + l^2}{a^3} \right) da$$

$$= -\frac{2}{a} \sin^2 \theta da$$

1

$$do = -(tan o) \left(\frac{da}{a}\right)$$

$$\Delta\theta \approx -\tan\theta \left(\frac{\Delta a}{a}\right) = -\tan\theta \left(\lambda\Delta T\right)$$

2

$$\Delta\theta \approx -0.0075$$
 tan Θ

(b) For the (111) reflection, evaluate $\Delta\Theta$.

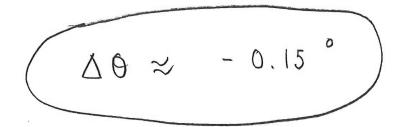
(10)

(III) reflection

$$\sin^2 \theta_{111} = \frac{3\lambda^2}{4\alpha^2} = \frac{3 \times (1.54)^2}{4 \times (4.05)^2} \approx .11$$

sm 0,11 & 0.33

tan 0,,, ~ 0.35



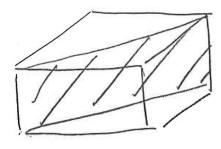
△0 ≈ -.00261 radians

2 a) What is the n=1 Bragg angle for reflection from the (110) planes in bcc iron (cube edge = 2.91 Å) for an X-ray wavelength of λ = 1.54 Å?

(10)

bragg's Law (n=1)

$$sin \theta = \frac{\lambda}{2d}$$



bec lattice

$$d = \frac{a}{\sqrt{h^2 + k^2 + \ell}}$$

$$d_{110} = \frac{a}{\sqrt{2}}$$

$$\sin \theta = \frac{\lambda}{2} \frac{\sqrt{2}}{a}$$

$$= \frac{(1.54)}{(2.91)} \frac{\sqrt{2}}{2} = .374$$

 $\theta = 21.96^{\circ} = 22^{\circ}$

b) Please calculate the density of bcc iron. You can take the atomic weight of Fe to be 56 and Avogadro's number $N = 6.02 \times 10^{23} \text{ mol}^{-1}$.



$$= \frac{2}{(2.91 \times 10^{-8})^3}$$

bcc lattice

$$= \frac{(2)(56)}{(2.91)^3(6)}$$
 10¹ g/cm³

8 onner atoms

& alls

N.B. Tenthork value p= 7.86 g/cm3

5

- 3. Please consider a monolayer of element X that is a two-dimensional array of X atoms in the fcc (100) surface. The cubic lattice constant is 4 Å.
 - a) Let us suppose that the phonon dispersion for this layer has the form What is the phonon density of states ((w)) for this 2-d solid?

$$N(k) = \pi k^{2} = \frac{A k^{2}}{4\pi}$$

$$\left(\frac{2\pi}{L}\right)^{2}$$



$$N(\omega) = A\omega^{2}$$

$$4\pi c^{2}$$

$$g(w) = 2 \frac{dN}{dw} = \frac{A w}{\pi c^2}$$

2 modes/k-print

(1 engitudinal, 1 tranverse)

b) The speed of sound in bulk X is $c = 5 \times 10^3$ m/s, and let's assume that this value is also appropriate for our monolayer. What is the Debye temperature for this X monolayer?

you may need these emistants
$$k = 1.05 \times 10^{-34} \text{ J-s}$$

$$k_B = 1.4 \times 10^{-23} \text{ J/k}$$

$$k_{B} \Theta_{0} = k_{W_{D}} \implies \Theta_{0} = \frac{k_{W_{D}}}{k_{B}}$$

$$2N(\omega_D) = 2N \Rightarrow \omega_D$$

$$\frac{A w_p^2}{4 \pi c^2} = 2N$$

$$w_{D} = \left\{ 4\pi c^{2} \left(\frac{N}{\Lambda} \right) \right\}^{1/2}$$

$$\frac{3}{1.4 \times 10^{-23}} = \frac{1.05 \times 10^{-34}}{1.4 \times 10^{-23}} = \frac{4\pi}{1.4 \times 10^{-23}} = \frac{4\pi}{1.4 \times 10^{-23}} = \frac{1.4 \times 10^{-23}}{1.4 \times 10^{-23}} = \frac{1.4 \times 10^{-23}}{1.4 \times 10^{-23}} = \frac{2\sqrt{14}}{1.4 \times 10^{-23}} = \frac{2\sqrt{14}}{1.4 \times 10^{-23}} = \frac{1.4 \times 10^{-23}}{1.4 \times 10^{-23}} = \frac{1.4 \times$$

$$= \frac{3.53 \times 10^{2} \text{ K}}{0.53 \times 10^{13} \text{ K}} = 4.7 \times 10^{13} \text{ s}^{-1}$$

2/all =

c) Using a Debye approach, please determine the temperature-dependence of the specific heat, $c_v(T)$, at low temperatures for this layer (you don't have to solve for all the coefficients and can leave them as definite integrals that are equal to constants).

$$U(\tau) = \int \frac{\hbar w \, g(w) \, dw}{\hbar w / k \tau}$$

$$\int_{0}^{\infty} \frac{h\omega}{mc^{2}} d\omega$$

$$\int_{0}^{\infty} \frac{h\omega/uT}{e} d\omega$$

$$\mathcal{R} = \frac{\hbar \omega}{kT}$$

$$\mathcal{R}_{c} = \frac{\hbar \omega}{kT}$$

$$\mathcal{R}_{c} = \frac{\hbar \omega}{kT} / \frac{k}{kT}$$

$$\lim_{T\to 0} u(T) = \frac{hA}{\pi c^2} \left(\frac{hT}{h}\right)^3 \int_{0}^{\frac{x^2}{4x}-4} \frac{x^2}{e^x-4}$$

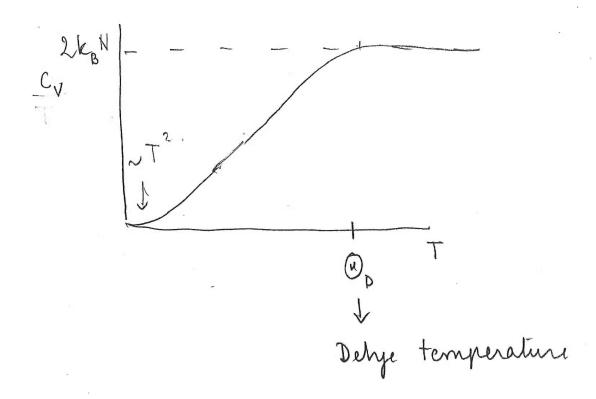
$$C_{V} = \begin{pmatrix} 0U \\ 0+ \end{pmatrix}_{V} = \begin{bmatrix} 1 & 1 & 2 \\ 0+ & 1 & 1 \end{pmatrix}$$

$$T \to 0 \qquad c_{V} = \begin{pmatrix} 0U \\ 0+ & 1 & 1 \end{pmatrix}$$

$$enstant = \begin{bmatrix} 1 & 1 & 1 \\ 0 & 1 &$$

d) Sketch the specific heat of the monolayer of X as a function of temperature, indicating important temperature scales.

(5)



4. a) Using a free electron model, please derive an expression for the radius of the Fermi sphere in k-space as a function of n where n is the electron concentration.

$$n = \frac{N}{V} = 2 \frac{1}{(2\pi)^3} \frac{4}{3} \pi k_F^3$$

$$n = \frac{1}{3\pi^2} k_F^3 = \frac{1}{3\pi^2} k_F = \frac{(3\pi^2 n)^{1/3}}{3\pi^2}$$

b) Monovalent Cu crystallizes in a fcc lattice with reciprocal lattice vectors

A =
$$2\pi/a$$
 (1, -1, 1)
B = $2\pi/a$ (1, 1, -1)
C = $2\pi/a$ (-1, 1, 1).

Brillouin

By determining the distance between the Fermi sphere and the zone face, please give an argument, within the nearly free electron model, for why fcc Cu is expected to be a good metal.

$$k_{i} = \frac{1}{2} \frac{l\pi}{a} \left(\frac{1}{1} + \frac{1}{2} + \frac{1}{2} \right) \frac{1}{2}$$

$$= \sqrt{3} \pi = 1.7 \frac{\pi}{a}$$

For
$$fcc$$
 ec $n = \frac{4}{a^3}$

$$k_{F} = \left(\frac{3\pi^{2}}{a^{3}}\right)^{1/3} = \left(\frac{12}{\pi}\right)^{1/3} \frac{\pi}{a}$$

$$= 1.5 \frac{\pi}{a}$$

hf L Iri

Fermi Surface does not touch

BZ faces => free electron pricture OK

V metal.



c) Please repeat the same calculation for divalent Zn in a fcc lattice. Discuss the expected electrical behavior based on the nearly free electron model.

$$n = \frac{8}{3}$$

$$J_{R_{\mathrm{F}}} = \left(\frac{3\pi^2}{\alpha^3} + \frac{4}{\alpha^3}\right)^{1/3} = \left(\frac{24}{\pi}\right)^{1/3}$$

Band gaps will churchally occur.

discribe system

Bands must be modified by portential. Free electron model must the modified to

- 5. Please answer the following conceptual questions.
 - a. What additional information would you request to determine whether a diffraction pattern is due to the scattering of charged particles or by electromagnetic radiation?

EM radiation
$$E = hf = \frac{hc}{\lambda} \Rightarrow \lambda = \frac{hc}{E}$$

For charged particles
$$\lambda = \frac{h}{h} = \frac{h}{\sqrt{2mE}} \Rightarrow \lambda = \frac{h}{\sqrt{2mE}}$$

$$(nm-relativestic)$$

$$\lambda(E)$$
 would distinguish there types of scattering

b. Vacancies are missing atoms in an otherwise near-perfect crystal. Since they create disorder and increase the entropy, vacancies are always present at nonzero temperatures. How would you expect the X-ray diffraction of a crystal to change due to presence of a small number of vacancies?

We expect unduced intensity in the Bragg quals (empared to those of a perfect crystal) and some untribution to background scattering. 4

c. What is the physical origin of the electronic gaps in the nearly free electron model? Please explain.

Bragg reflection is the physical origin of the gaps in the electronic spectrum. The Bragg condition, $k=\pm\frac{1}{2}G$, means that there is Bragg reflection at the Brillman your boundaries thus, here there will be no travelling were solutions and only standing waves — hence the energy gaps at the BZBs.

d. What are quasicrystals and why was their discovery so controversial? (4) Quaricrystals are solids where atoms are arranged in neither periodie no random structure. Before their identification it was believed that sharp diffraction sports implied translational symmetry. However the diffraction patterns of quaricrystalline materials are sharp and display "Inhidden symmetries" known its be incompatible of space-filling structures. they defied the enventioned misdom of diffraction and initially many thought that thin Bragg characterization could be explained by twinning or (random)

4

e. Please explain how "anti-Bragg" scattering is used to monitor surface growth in samples.

In the anti-Bragg emdition, the source, the sample and the ditector on set up so that there is distructive interference between parallel planes in the enjstablene sample. In this situation, specular infliction from the surface can be monitored to give information about layer-by-layer growth.